Alignment Mark and Method of Formation

ABSTRACT OF THE DISCLOSURE

In accordance with an embodiment, a structure comprises a substrate having a first area and a second area; a through substrate via (TSV) in the substrate penetrating the first area of the substrate; an isolation layer over the second area of the substrate, the isolation layer having a recess; and a conductive material in the recess of the isolation layer, the isolation layer being disposed between the conductive material and the substrate in the recess.

Figure 1A